

# Artem V Rykov

## List of Publications by Year in descending order

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17  
papers

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citations

1937457

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1719901

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docs citations

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times ranked

59  
citing authors

#	ARTICLE	IF	CITATIONS
1	Electrically pumped InGaAs/GaAs quantum well microdisk lasers directly grown on Si(100) with Ge/GaAs buffer. Optics Express, 2017, 25, 16754.	1.7	13
2	MOCVD Growth of InGaAs/GaAs/AlGaAs Laser Structures with Quantum Wells on Ge/Si Substrates. Crystals, 2018, 8, 311.	1.0	11
3	On the stimulated emission of InGaAs/GaAs/AlGaAs laser structures grown by MOCVD on exact and inclined Ge/Si(001) substrates. Semiconductors, 2017, 51, 663-666.	0.2	5
4	Peculiarities of growing InGaAs/GaAs/AlGaAs laser structures by MOCVD on Ge/Si substrates. Semiconductors, 2017, 51, 1527-1530.	0.2	5
5	Technology of the production of laser diodes based on GaAs/InGaAs/AlGaAs structures grown on a Ge/Si substrate. Semiconductors, 2017, 51, 1477-1480.	0.2	4
6	Methods for spin injection managing in InGaAs/GaAs/Al <sub>2</sub> O <sub>3</sub> /CoPt spin light-emitting diodes. Physics of the Solid State, 2017, 59, 2155-2161.	0.2	4
7	Heterostructures with InGaAs/GaAs quantum dots doped with transition elements: II. Study of the circularly polarized luminescence. Technical Physics, 2017, 62, 1545-1550.	0.2	4
8	Temperature stabilization of spin-LEDs with a CoPt injector. Journal of Physics: Conference Series, 2017, 816, 012034.	0.3	3
9	On the Application of Strain-Compensating GaAsP Layers for the Growth of InGaAs/GaAs Quantum-Well Laser Heterostructures Emitting at Wavelengths above 1100 nm on Artificial Ge/Si Substrates. Semiconductors, 2018, 52, 1547-1550.	0.2	3
10	Effect of the dopant concentration on the luminescence properties of InGaAs/GaAs spin light-emitting diodes with a Mn δ layer. Semiconductors, 2016, 50, 1-7.	0.2	2
11	Structural investigation of light-emitting Al <sub>0.5</sub> B <sub>0.5</sub> structures grown on Ge/Si(100) substrate. Journal of Physics: Conference Series, 2018, 1124, 022037.	0.3	2
12	Structural and optical characteristics of GaAs films grown on Si/Ge substrates. Journal of Physics: Conference Series, 2018, 993, 012014.	0.3	2
13	Control of circular polarization of electroluminescence in spin light-emitting diodes based on InGaAs/GaAs/δ-Ce <sup>2+</sup> /Mn <sup>2+</sup> heterostructures. Physics of the Solid State, 2017, 59, 2162-2167.	0.2	1
14	Studies of the Cross Section and Photoluminescence of a GaAs Layer Grown on a Si/Al <sub>2</sub> O <sub>3</sub> Substrate. Semiconductors, 2019, 53, 1242-1245.	0.2	1
15	Temperature dependence of the circular polarization of electroluminescence from spin-polarized light-emitting diodes based on InGaAs/GaAs heterostructures. Journal of Surface Investigation, 2014, 8, 433-439.	0.1	0
16	1.06 μm wavelength photodetectors with metamorphic buffer layers grown on GaAs substrates. Journal of Physics: Conference Series, 2018, 1124, 041037.	0.3	0
17	Stimulated Emission at 1.3 μm Wavelength in Metamorphic InGaAs/InGaAsP Structure with Quantum Wells Grown on Ge/Si(001) Substrate. Technical Physics Letters, 2018, 44, 735-738.	0.2	0